

2SA1597, 2SC4146



2018A

PNP/NPN Epitaxial Planar
Silicon Transistors

T-37-13

T-35-11

Switching Applications

(with Bias Resistances $R_1=4.7k\Omega$, $R_2=47k\Omega$)

©2480

Applications

- Switching circuit, inverter circuit, interface circuit, driver circuit

Features

- On-chip bias resistance ($R_1=4.7k\Omega$, $R_2=47k\Omega$)
- Small-sized package (CP)

(): 2SA1597

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	(-)50	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)100	mA
Peak Collector Current	i_{cp}	(-)200	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

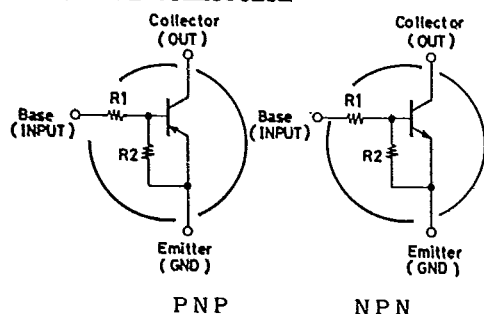
Electrical Characteristics at $T_a=25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)40\text{V}, I_E=0$		(-)0.1		μA
Collector Cutoff Current	I_{CE0}	$V_{CE}=(-)40\text{V}, I_B=0$		(-)0.5		μA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=(-)5\text{V}, I_C=0$	(-)74	(-)97	(-)138	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5\text{V}, I_C=(-)5\text{mA}$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)5\text{mA}$		250		MHz
				(200)		
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		3.5		pF
				(5.3)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10\text{mA}, I_B=(-)0.5\text{mA}$		(-)0.1	(-)0.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu\text{A}, R_{BE}=\infty$	(-)50			V

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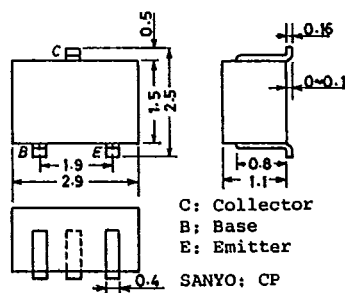
Marking 2SA1597:XL, 2SC4146:FT

Electrical Connection



Case Outline 2018A

(unit:mm)



4107TA, TS No.2480-1/2

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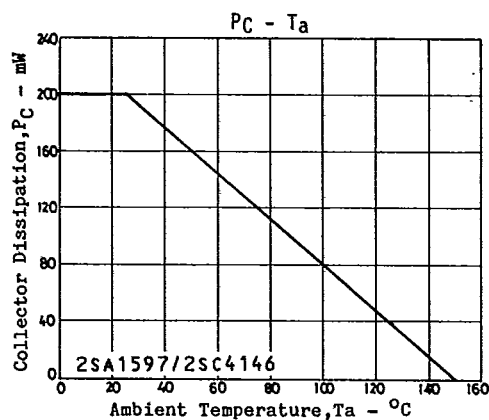
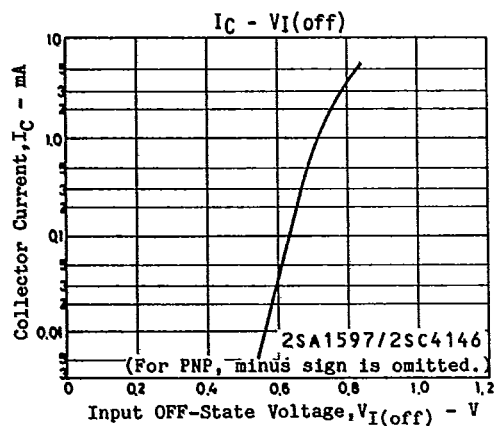
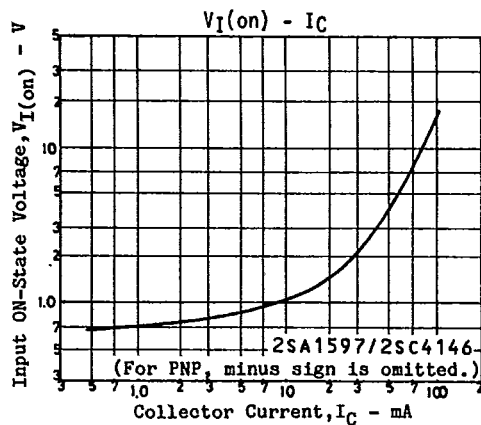
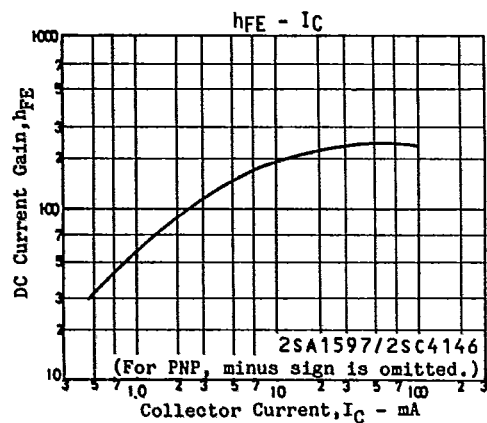
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		min	typ	max	unit
Input OFF-State Voltage	$V_{I(off)}$ $V_{CE}=(-)5V, I_C=(-)100\mu A$	$(-)0.5$	$(-)0.6$	$(-)0.8$	V
Input ON-State Voltage	$V_{I(on)}$ $V_{CE}=(-)0.2V, I_C=(-)5mA$	$(-)0.7$	$(-)0.85$	$(-)1.3$	V
Input Resistance	R_I	3.3	4.7	6.1	kohm
Resistance Ratio	R_1/R_2	0.09	0.1	0.11	

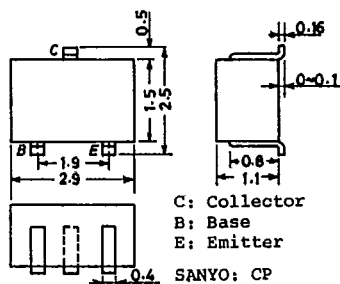


T-91-20

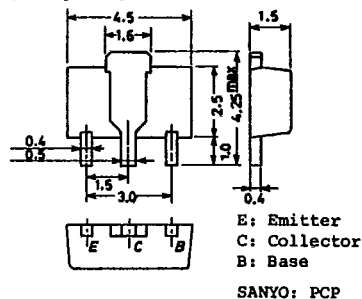
CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

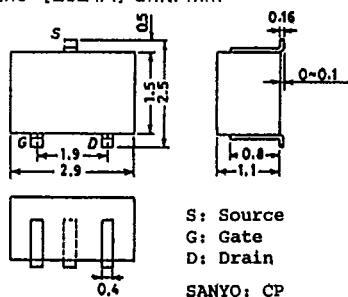
Case Outline—[2018A] unit: mm



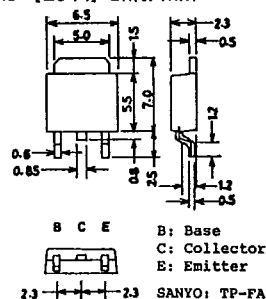
Case Outline—[2038] unit: mm



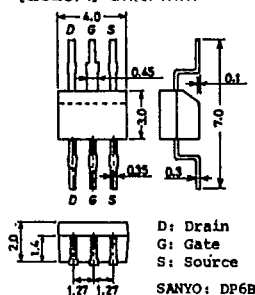
Case Outline—[2024A] unit: mm



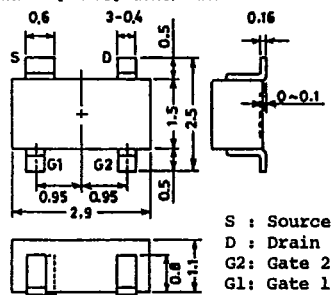
Case Outline—[2044] unit: mm



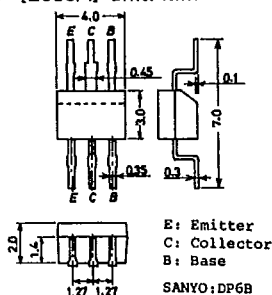
Case Outline—[2028A] unit: mm



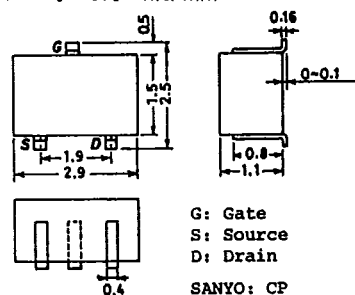
Case Outline—[2046] unit: mm



Case Outline—[2030A] unit: mm

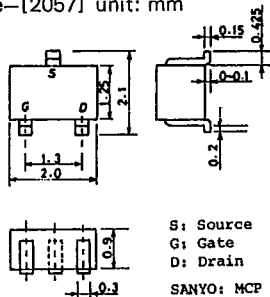


Case Outline—[2050] unit: mm

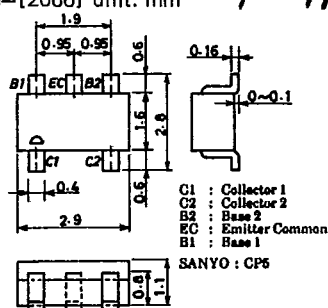


T-91-20

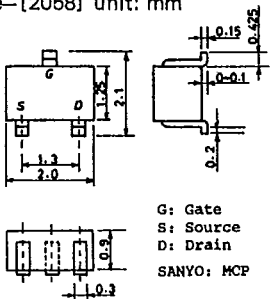
Case Outline—[2057] unit: mm



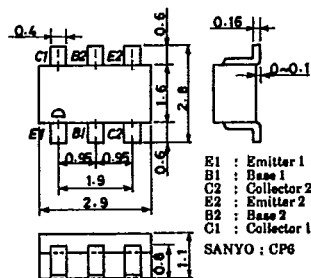
Case Outline—[2066] unit: mm



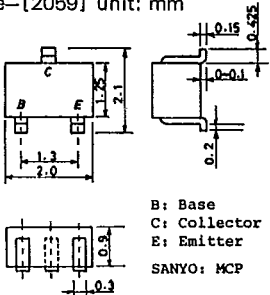
Case Outline—[2058] unit: mm



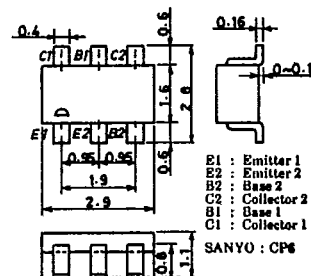
Case Outline—[2067] unit: mm



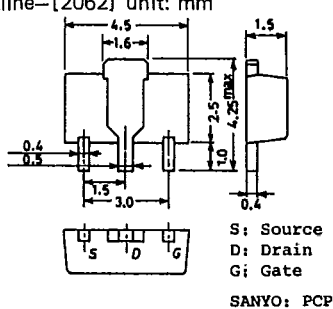
Case Outline—[2059] unit: mm



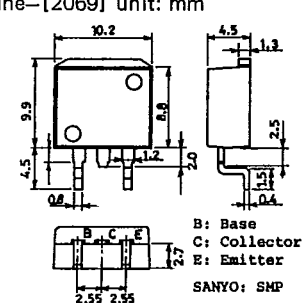
Case Outline—[2068] unit: mm



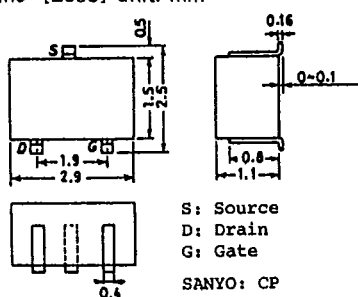
Case Outline—[2062] unit: mm



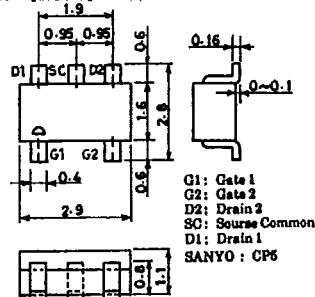
Case Outline—[2069] unit: mm



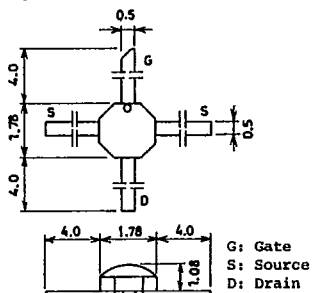
Case Outline—[2065] unit: mm



Case Outline—[2070] unit: mm

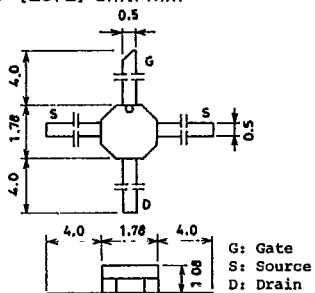


Case Outline-[2071] unit: mm



T-9120

Case Outline-[2072] unit: mm



Case Outline-[2073] unit: mm

